MSKSEMI















ESD

TVS

TSS

MOV

GDT

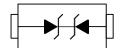
PLED

Broduct data sheet





SOD-923



Feature

80W peak pulse power per line ($t_P = 8/20\mu s$)

SOD-923 package

Replacement for MLV(0402)

Bidirectional configurations

Response time is typically < 1ns

Low clamping voltage

RoHS compliant

Transient protection for data lines to

EC61000-4-2(ESD) ±30KV(air), ±30KV(contact);

IEC61000-4-4 (EFT) 40A (5/50ns)

Applications

Cellular phones

Portable devices

Digital cameras

Power supplies

Mechanical Characteristics

Lead finish:100% matte Sn(Tin)

Mounting position: Any

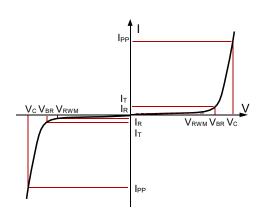
Device meets MSL 1 requirements

Pure tin plating: 7 ~ 17 um

Pin flatness:≤3mil

Electronics Parameter

Symbol	Parameter			
V _{RWM}	Peak Reverse Working Voltage			
I _R	Reverse Leakage Current @ V _{RWM}			
V_{BR}	Breakdown Voltage @ I⊤			
Ι _Τ	Test Current			
I _{PP}	Maximum Reverse Peak Pulse Current			
Vc	Clamping Voltage @ I _{PP}			
P _{PP}	Peak Pulse Power			
CJ	Junction Capacitance			
I _F	Forward Current			
V _F	Forward Voltage @ I _F			



Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Units
Peak Reverse Working Voltage	V _{RWM}				5	V
Breakdown Voltage	V_{BR}	I _t = 1mA	5.6	6.7	7.8	V
Reverse Leakage Current	I _R	V _{RWM} = 5V T=25℃			1.0	μA
Maximum Reverse Peak Pulse Current	I _{PP}			5		Α
Clamping Voltage	Vc	I _{PP} =1A			8	V
Clamping Voltage	Vc	I _{PP} =3A			13	V
Clamping Voltage	Vc	I _{PP} =5A			15	V
Junction Capacitance	C _j	V _R =0V f = 1MHz		12	15	pF

Absolute maximum rating@25℃

Rating	Symbol	Value	Units
Peak Pulse Power (t _p =8/20µs)	P _{pp}	80	W
Operating Temperature	TJ	-55 to +150	$^{\circ}\!\mathrm{C}$
Storage Temperature	T _{STG}	-55 to +150	$^{\circ}$ C

Typical Characteristics

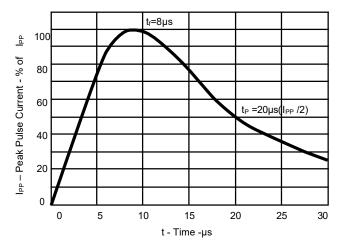


Fig 1.Pulse Waveform

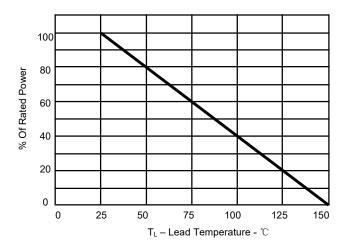


Fig 2.Power Derating Curve



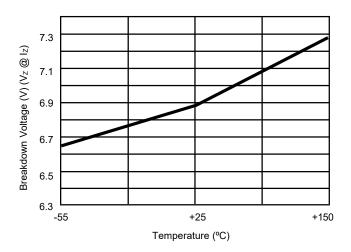


Fig 3.Typical Breakdown Voltage vs. Temperature

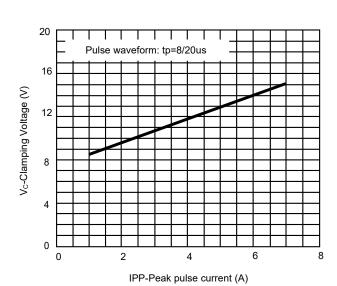


Fig 5. Clamping voltage vs. Peak pulse current

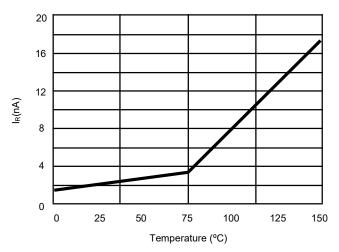


Fig 4. Typical Leakage Current vs. Temperature

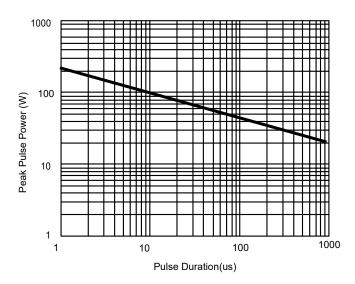
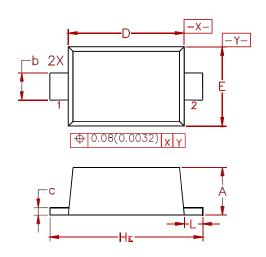


Fig 6. Non-Repetitive Peak Pulse Power vs. Pulse time

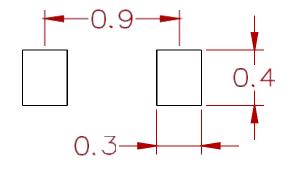


PACKAGE MECHANICAL DATA



Dim	Millimeters			Inches			
	Min	Nom	Max	Min	Nom	Max	
Α	0.36	0.40	0.43	0.014	0.016	0.017	
b	0.15	0.20	0.25	0.006	0.008	0.010	
С	0.07	0.12	0.17	0.003	0.005	0.007	
D	0.75	0.80	0.85	0.030	0.031	0.033	
E	0.55	0.60	0.65	0.022	0.024	0.026	
HE	0.95	1.00	1.05	0.037	0.039	0.041	
L	0.05	0.10	0.15	0.002	0.004	0.006	

Suggested Pad Layout



Dimensions: Millimeters

REEL SPECIFICATION

P/N	PKG	QTY
ESD9X5.0ST5G	SOD-923	8000



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